N-Channel Super Junction Power MOSFET Ⅳ

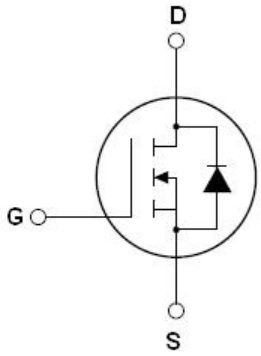
General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode.This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications,Fast charger, new energy vehicle charging pile, on-board OBC etc.

$V_{DS\ min@Tjmax}$	650	V
$R_{DS(ON)TYP}$	95	mΩ
ID	29	A
Qg	41	nC

Features

- ●New technology for high voltage device
- ●Ultra low on-resistance and ultra low conduction losses
- ●Ultra Low Gate Charge cause lower driving requirements
- ●Diode reverse recovery speed is super fast
- ●High reliability
- ●ROHS compliant&Halogen Free



Schematic diagram

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- On-board charger(OBC)

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE60NF110	TO-220-3L	NCE60NF110

TO-220

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	600	V
Gate-Source Voltage (V_{DS}=0V) AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	29	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	20.3	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	87	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	241 1.60	W W/°C
Avalanche current**(Note 1)**	I_{AS}	7	A
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.62	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	600			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			400	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=14A		95	110	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		2161		pF
Output Capacitance	C_{oss}			95		pF
Reverse Transfer Capacitance	C_{rss}			50		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=14A, V_{GS}=10V		41.2		nC
Gate-Source Charge	Q_{gs}			16.3		nC
Gate-Drain Charge	Q_{gd}			12.8		nC
Gate plateau voltage	Vgp			7.0		V
Intrinsic gate resistance	R_G	f = 1 MHz open drain		1.5		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=14A, R_G=1.7Ω,V_{GS}=10V		32		nS
Turn-on Rise Time	t_r			15		nS
Turn-Off Delay Time	$t_{d(off)}$			90		nS
Turn-Off Fall Time	t_f			8		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			29	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				87	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=29A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=14A,di/dt=100A/μs		115		nS
Reverse Recovery Charge	Q_{rr}			0.47		uC
Peak Reverse Recovery Current	I_{rrm}			8		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Source-Drain Diode Forward Voltage

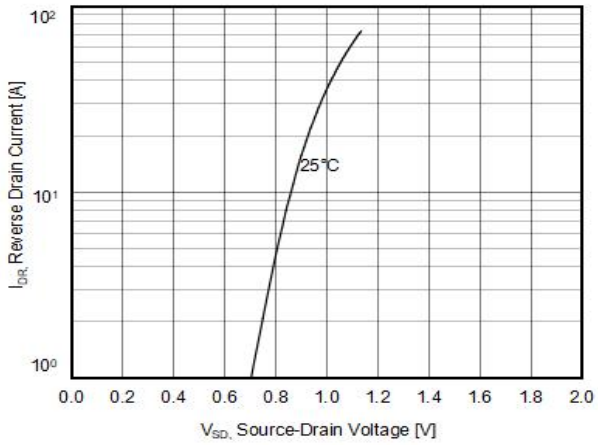


Figure2. Maximum I_D vs Junction Temperature

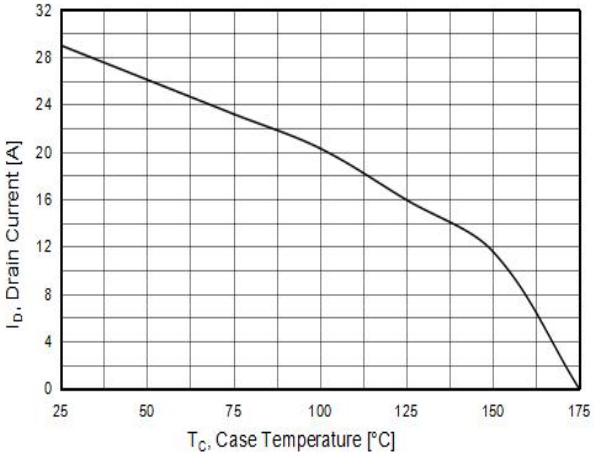


Figure3. Static drain-source on resistance

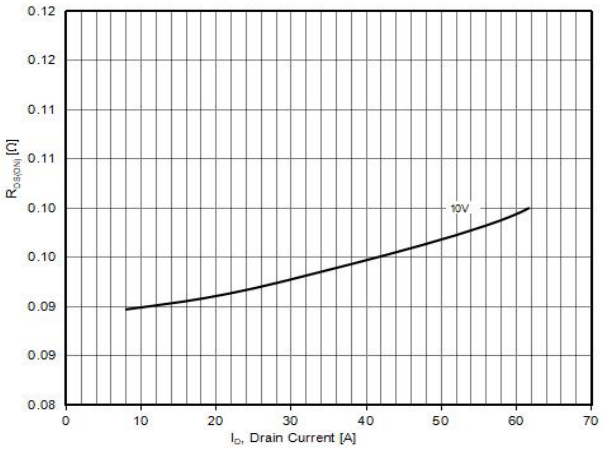


Figure4. Transfer characteristics

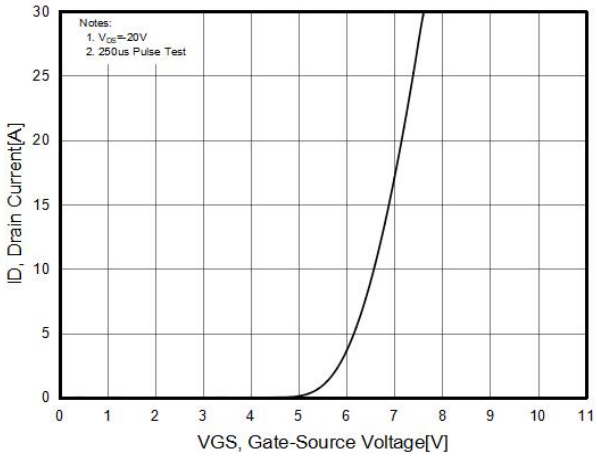


Figure5. $R_{DS(ON)}$ vs Junction Temperature

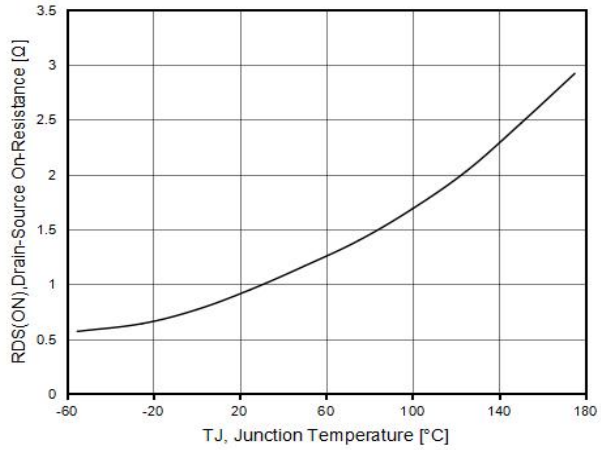
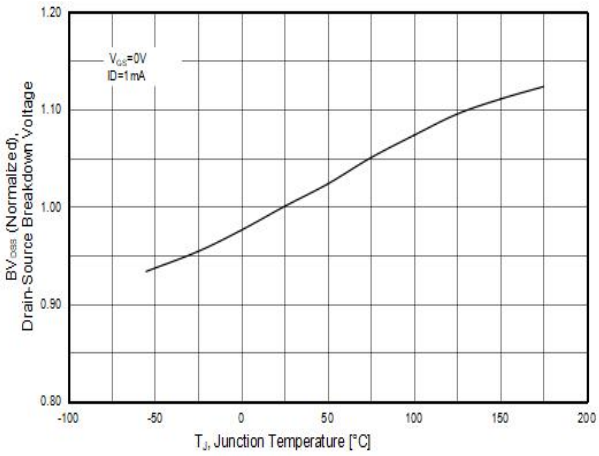
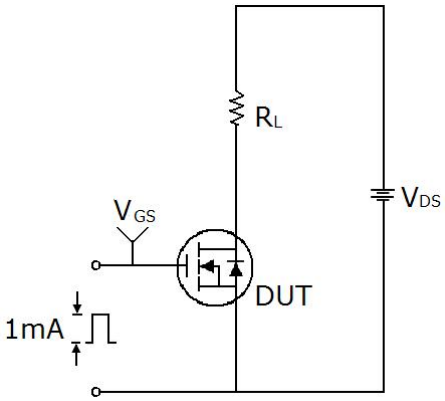


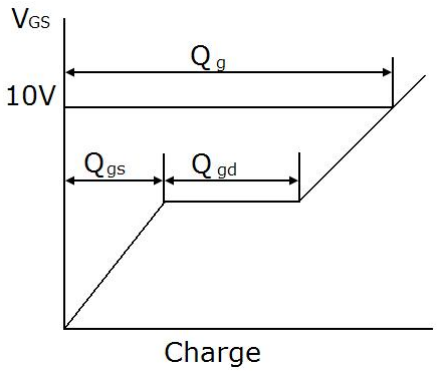
Figure6. BV_{DSS} vs Junction Temperature



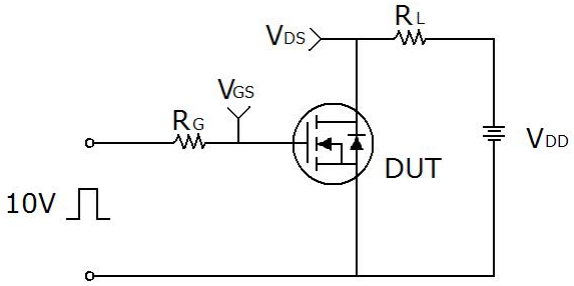
Test circuit

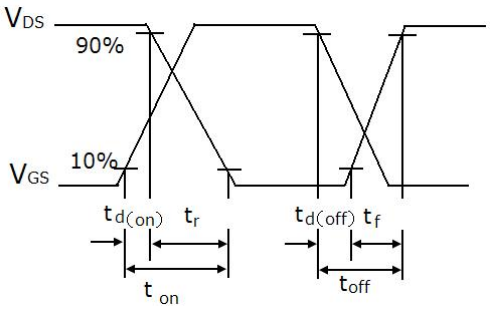
1）Gate charge test circuit & Waveform



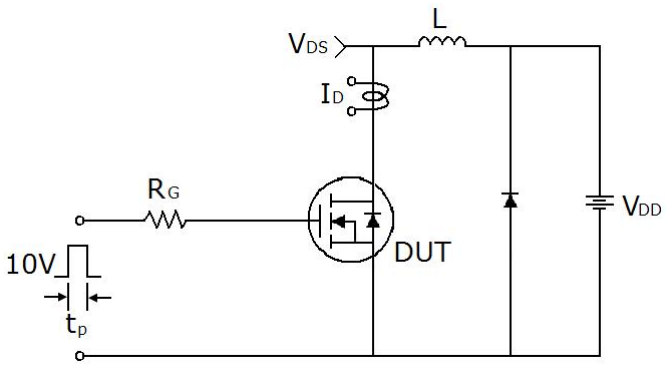


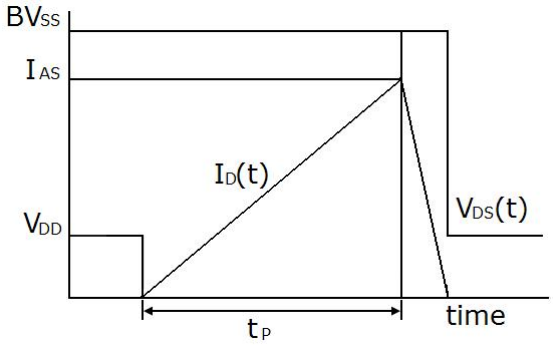
2）Switch Time Test Circuit：



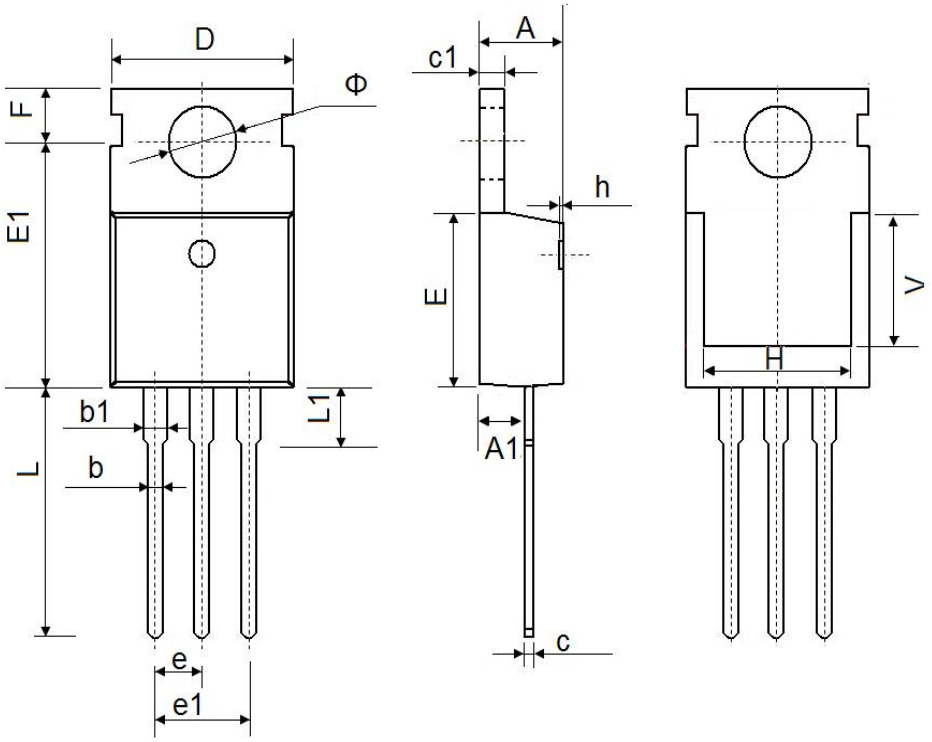


3）Unclamped Inductive Switching Test Circuit & Waveforms



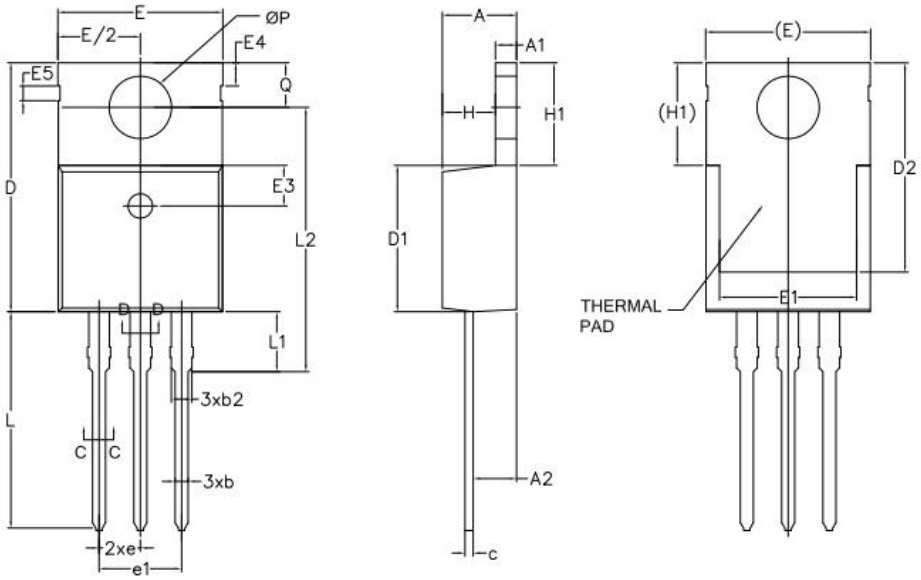


TO-220-3L-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.20	4.60	0.165	0.181
A1	2.25	2.55	0.089	0.100
b	0.70	0.90	0.028	0.035
b1	1.17	1.37	0.046	0.054
c	0.33	0.65	0.013	0.026
c1	1.20	1.40	0.047	0.055
D	8.95	9.75	0.352	0.384
E	9.74	10.04	0.352	0.384
E1	9.91	10.25	0.390	0.404
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	15.45	15.85	0.608	0.624
L	12.90	13.40	0.508	0.528
L1	2.85	3.25	0.112	0.128
Φ	3.40	3.80	0.134	0.150

TO-220-3L-J Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.47	4.67	0.176	0.184
A1	1.20	1.40	0.047	0.055
A2	2.35	2.90	0.093	0.114
b	0.71	0.91	0.028	0.036
b1	0.71	0.86	0.028	0.034
b2	1.22	1.36	0.048	0.054
c	0.47	0.60	0.019	0.024
c1	0.47	0.55	0.019	0.022
D	14.70	15.80	0.579	0.622
D1	8.90	9.47	0.350	0.373
D2	11.75	13.60	0.463	0.535
E	9.70	10.37	0.382	0.408
E1	7.00	8.89	0.276	0.350
E2	9.80	10.20	0.386	0.402
E3	2.40	2.60	0.094	0.102
E4	1.27	1.57	0.050	0.062
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	3.00	3.40	0.118	0.134
L	12.90	14.80	0.508	0.583
L1	2.54	3.84	0.100	0.151
L2	12.13	16.50	0.478	0.650
ΦP	3.60	3.90	0.142	0.154
Q	4.60	4.90	0.181	0.193

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